

NPN SILICON EPITAXIAL TRANSISTOR
L Band Power Amplifier

DESCRIPTION AND APPLICATIONS

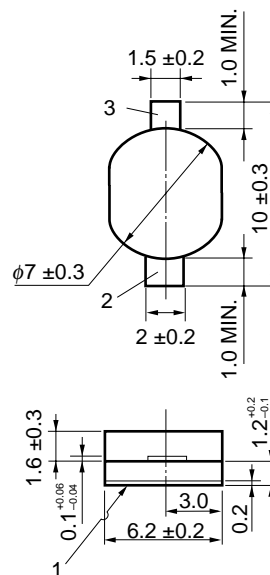
NEL2001012-24 of NPN epitaxial microwave power transistors is designed for 1.8-2 GHz PHS/PCN/PCS base station applications.

It incorporates emitter ballast resistors, gold metallizations and offers a high degree of reliability.

FEATURES

- High Linear Power and Gain
- Low Internal Modulation Distortion
- High Reliability Gold Metallization
- Emitter Ballasting
- 24 V Operation

OUTLINE DIMENSIONS (Unit: mm)



1 - EMITTER
2 - BASE
3 - COLLECTOR

ABSOLUTE MAXIMUM RATING (T_A = 25 °C)

PARAMETER	SYMBOL	SPECIFIED CONDITION	RATINGS	UNIT
Collector to Base Voltage	V _{CBO}		45	V
Collector to Emitter Voltage	V _{CER}	R = 10 Ω	30	V
Emitter to Base Voltage	V _{EBO}		3	V
Collector to Emitter Voltage	V _{CEO}		18	V
Collector Current	I _c		0.5	A
Power Dissipation	P _T		7.4	W
Thermal Resistance	R _{th(j-c)}		23.6	°C/W
Junction Temperature	T _j		200	°C
Storage Temperature	T _{stg}		-65 to 150	°C

ELECTRICAL CHARACTERISTICS (T_A = 25 °C)

PARAMETER	SYMBOL	SPECIFIED CONDITION	MIN.	TYP.	MAX.	UNIT
Collector to Emitter Cutoff Current	I _{CES}	V _{CE} = 24 V			1	mA
Collector to Emitter Voltage (Base to Emitter Resistor = 10 Ω)	V _{CER}	I _C = 1 mA, R = 10 Ω	30	85		V
Collector to Emitter Voltage (Open Base)	V _{CEO}	I _C = 1 mA	18	22		V
Collector to Base Voltage (Open Emitter)	V _{CBO}	I _C = 1 mA	45	85		V
Emitter to Base Voltage (Open Collector)	V _{EBO}	I _C = 3 mA	3	4.4		V
DC Forward Current Gain	h _{FE}	V _{CE} = 5 V, I _C = 0.1 A	30	100	150	
Output Capacitance	C _{ob}	V _{CE} = 24 V, f = 1 MHz		3		pF

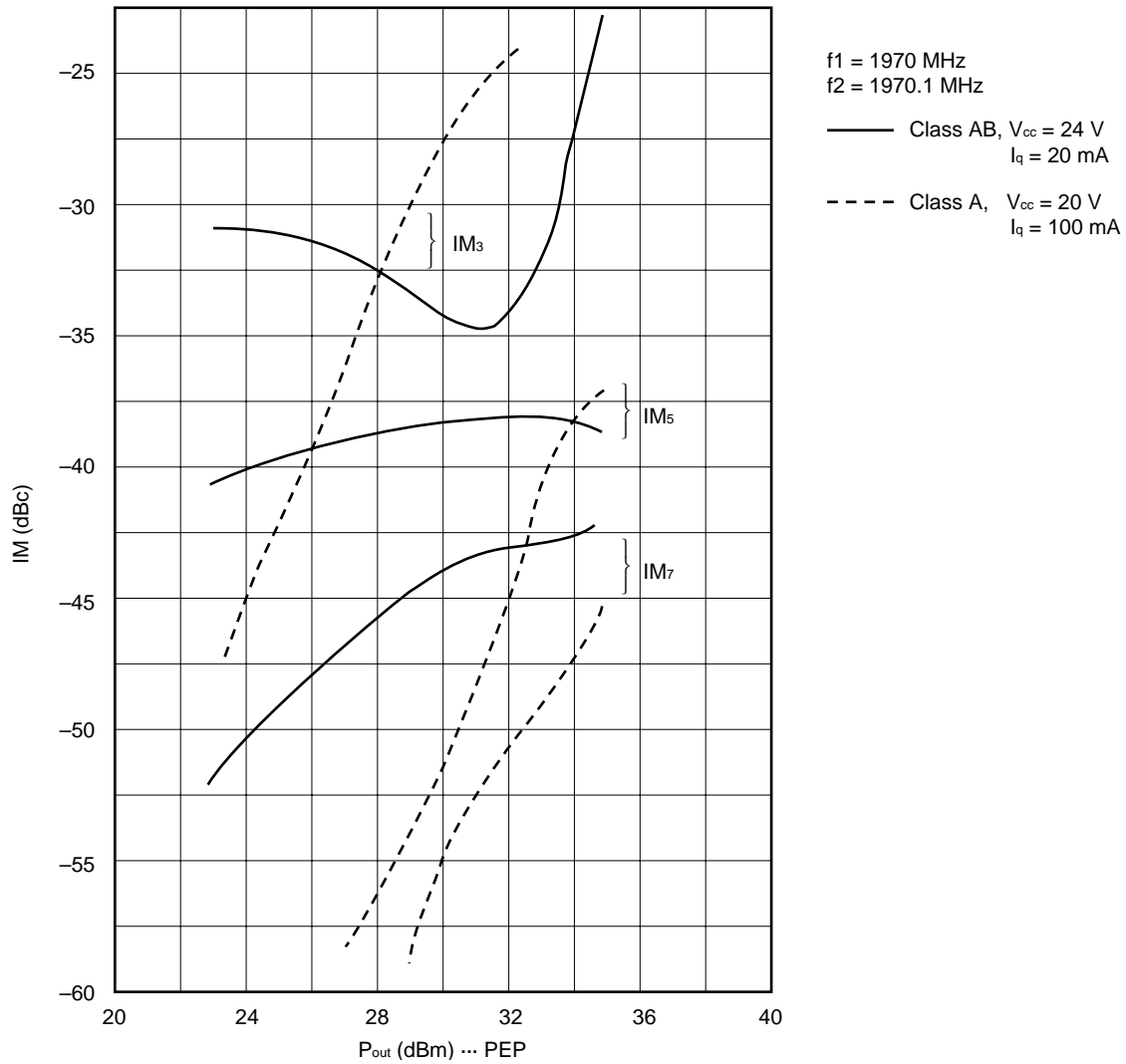
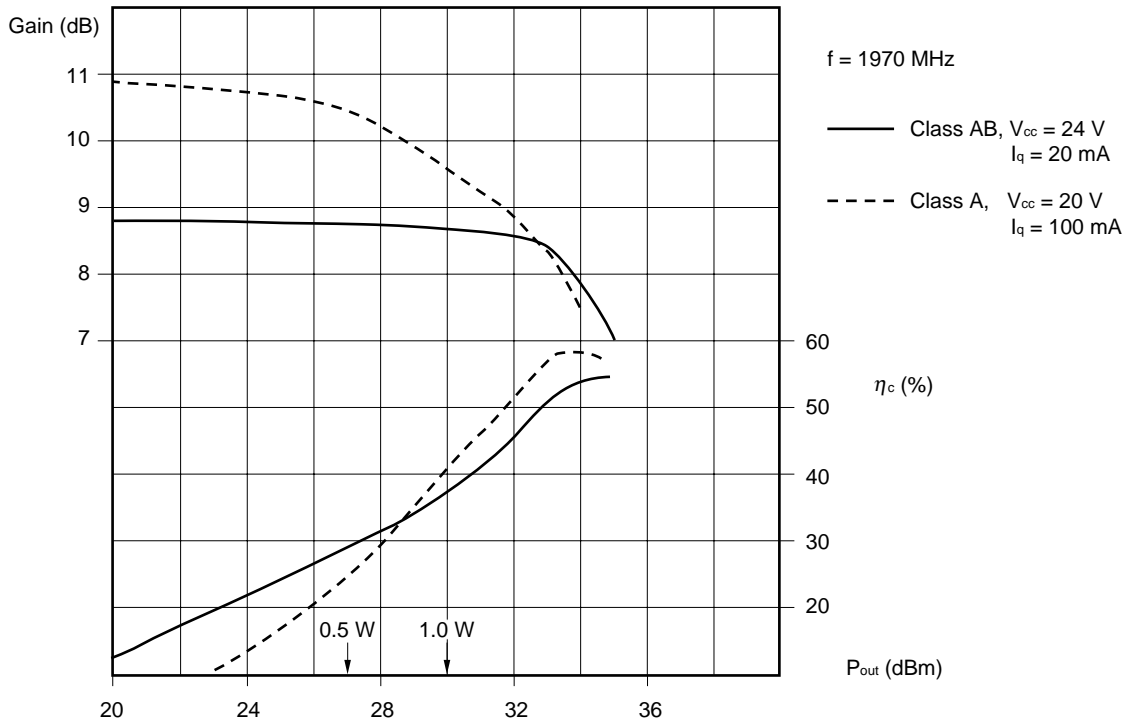
PERFORMANCE SPECIFICATIONS (T_A = 25 °C)

CLASS AB OPERATION

PARAMETER	SYMBOL	SPECIFIED CONDITION	MIN.	TYP.	MAX.	UNIT
Output Power	P _{ldB}	f = 1.97 GHz, I _q = 20 mA, V _{CC} = 24 V, CLASS AB		2.5		W
Collector Efficiency	η _C	f = 1.97 GHz, P _{out} = P _{ldB} , I _q = 20 mA, V _{CC} = 24 V, CLASS AB		54		%
Linear Gain	GL	f = 1.97 GHz, P _{in} = 0.04 W, I _q = 20 mA, V _{CC} = 24 V, CLASS AB		8.8		dB
3rd Order Intermodulation	IM ₃	f = 1.97 GHz, Δf = 100 kHz, 2 W PEP, V _{CC} = 24 V, I _q = 20 mA, CLASS AB		-33		dBc

CLASS A OPERATION

PARAMETER	SYMBOL	SPECIFIED CONDITION	MIN.	TYP.	MAX.	UNIT
Output Power	P _{ldB}	f = 1.97 GHz, I _q = 100 mA, V _{CC} = 20 V, CLASS A	0.5	0.7		W
Collector Efficiency	η _C	f = 1.97 GHz, P _{out} = P _{ldB} , I _q = 100 mA, V _{CC} = 20 V, CLASS A		30		%
Linear Gain	GL	f = 1.97 GHz, P _{in} = 0.01 W, I _q = 100 mA, V _{CC} = 20 V, CLASS A		10.8		dB
3rd Order Intermodulation	IM ₃	f = 1.97 GHz, Δf = 100 kHz, 0.5 W PEP, V _{CC} = 20 V, I _q = 100 mA, CLASS A		-36		dBc



S-PARAMETER

NEL2001 Class A

V_{CC} = 20 V, I_{cq} = 0.1 A

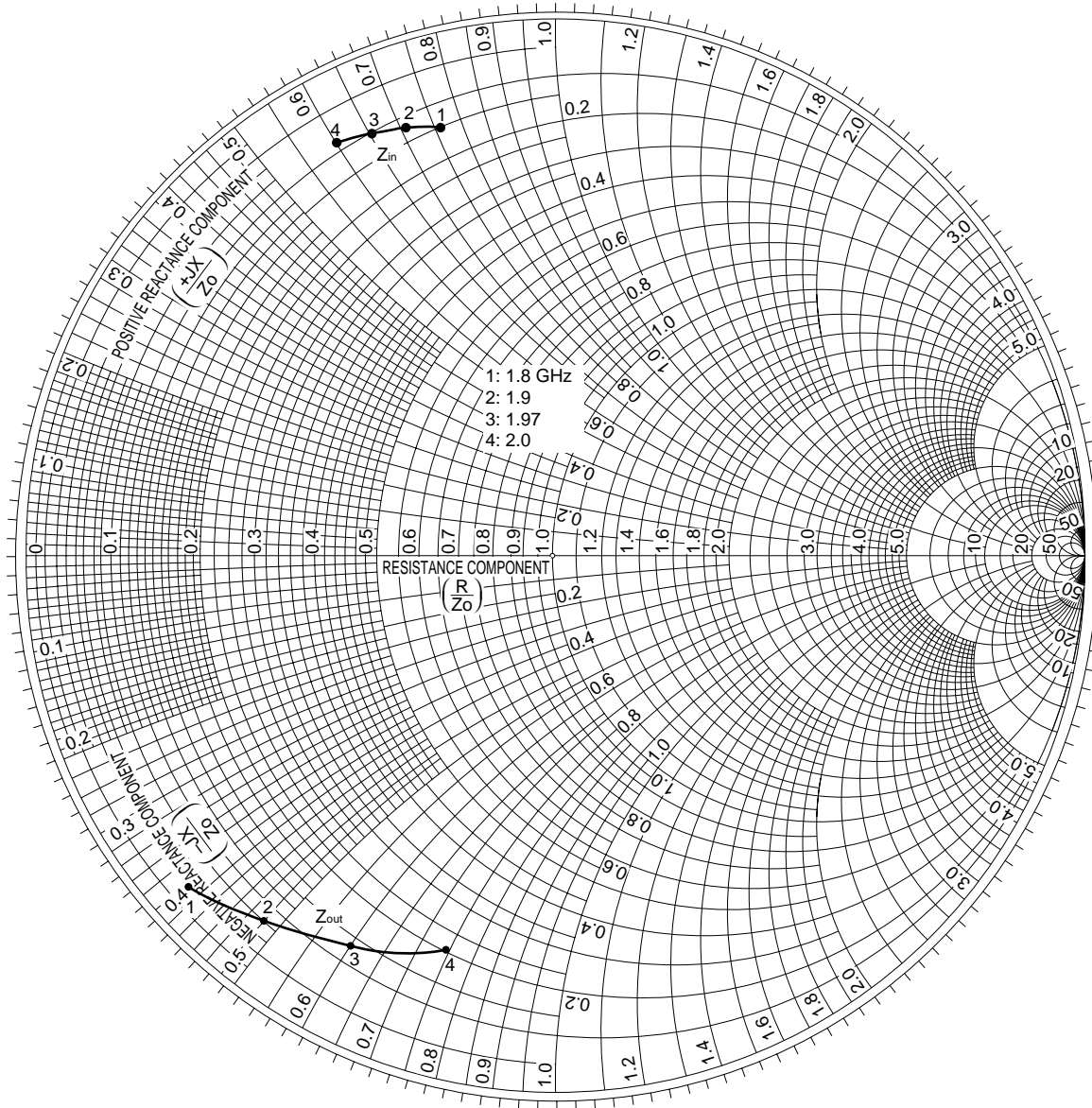
FREQUENCY GHz	MAG	S ₁₁ ANG (DEG)	MAG	S ₁₂ ANG (DEG)	MAG	S ₂₁ ANG (DEG)	MAG	S ₂₂ ANG (DEG)
1.70	0.75	130	0.07	-7	2.08	18	0.41	-155
1.71	0.75	129	0.07	-6	2.07	18	0.41	-155
1.72	0.74	129	0.07	-6	2.06	18	0.42	-156
1.73	0.74	128	0.08	-7	2.05	17	0.42	-156
1.74	0.74	128	0.08	-7	2.04	16	0.42	-156
1.75	0.74	127	0.08	-7	2.02	16	0.42	-156
1.76	0.74	127	0.08	-6	2.01	16	0.42	-156
1.77	0.74	127	0.08	-7	2.00	15	0.42	-156
1.78	0.74	126	0.08	-7	1.99	15	0.42	-157
1.79	0.74	126	0.08	-8	1.98	14	0.42	-157
1.80	0.74	125	0.08	-8	1.97	14	0.43	-157
1.81	0.74	125	0.07	-9	1.95	13	0.43	-157
1.82	0.74	124	0.07	-10	1.94	13	0.43	-158
1.83	0.74	124	0.08	-7	1.93	12	0.43	-158
1.84	0.74	124	0.08	-6	1.93	12	0.43	-158
1.85	0.75	124	0.08	-6	1.92	12	0.43	-158
1.86	0.75	123	0.08	-8	1.91	11	0.43	-158
1.87	0.75	122	0.08	-9	1.89	10	0.43	-159
1.88	0.75	122	0.08	-9	1.88	10	0.43	-159
1.89	0.75	122	0.08	-10	1.87	10	0.43	-159
1.90	0.75	121	0.08	-9	1.86	9	0.43	-159
1.91	0.75	121	0.08	-9	1.86	9	0.43	-159
1.92	0.75	120	0.08	-10	1.85	8	0.44	-159
1.93	0.75	120	0.08	-10	1.84	8	0.44	-160
1.94	0.75	119	0.08	-10	1.83	8	0.44	-160
1.95	0.75	119	0.08	-10	1.81	7	0.44	-160
1.96	0.75	119	0.08	-10	1.80	7	0.44	-161
1.97	0.75	118	0.08	-9	1.80	7	0.44	-161
1.98	0.75	118	0.08	-9	1.80	6	0.44	-161
1.99	0.75	118	0.08	-10	1.80	6	0.44	-161
2.00	0.75	117	0.08	-11	1.80	5	0.45	-161

NEL2001 Class AB

V_{CC} = 24 V, I_{cq} = 0.02 A

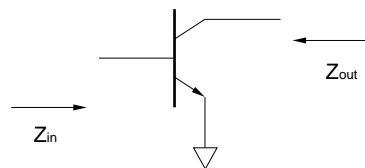
FREQUENCY GHz	MAG	S ₁₁ ANG (DEG)	MAG	S ₁₂ ANG (DEG)	MAG	S ₂₁ ANG (DEG)	MAG	S ₂₂ ANG (DEG)
1.70	0.78	131	0.07	-11	1.56	9	0.53	-132
1.71	0.78	130	0.06	-11	1.53	9	0.53	-132
1.72	0.78	130	0.06	-11	1.51	9	0.53	-133
1.73	0.78	130	0.07	-10	1.51	8	0.53	-133
1.74	0.77	129	0.07	-11	1.52	8	0.53	-133
1.75	0.77	129	0.07	-11	1.51	7	0.53	-134
1.76	0.77	128	0.07	-11	1.50	6	0.53	-134
1.77	0.77	128	0.06	-11	1.48	6	0.54	-134
1.78	0.77	128	0.06	-11	1.46	6	0.54	-135
1.79	0.77	127	0.06	-11	1.46	5	0.54	-135
1.80	0.77	127	0.06	-11	1.46	5	0.54	-135
1.81	0.78	127	0.07	-13	1.46	4	0.54	-135
1.82	0.78	126	0.07	-14	1.45	3	0.55	-136
1.83	0.78	126	0.07	-14	1.43	3	0.55	-136
1.84	0.77	125	0.07	-13	1.41	3	0.55	-137
1.85	0.77	125	0.07	-13	1.41	2	0.55	-137
1.86	0.78	124	0.07	-12	1.41	2	0.55	-137
1.87	0.78	124	0.07	-12	1.41	1	0.55	-138
1.88	0.78	123	0.07	-12	1.40	0	0.55	-138
1.89	0.78	123	0.07	-12	1.38	0	0.55	-138
1.90	0.78	122	0.07	-12	1.37	0	0.55	-139
1.91	0.78	122	0.07	-12	1.36	0	0.56	-139
1.92	0.78	121	0.07	-13	1.37	-1	0.56	-139
1.93	0.78	121	0.07	-13	1.37	-2	0.56	-140
1.94	0.78	121	0.07	-13	1.35	-2	0.56	-140
1.95	0.78	120	0.07	-13	1.34	-3	0.56	-140
1.96	0.78	120	0.07	-12	1.32	-3	0.56	-141
1.97	0.78	120	0.07	-12	1.32	-3	0.56	-141
1.98	0.78	119	0.07	-12	1.32	-3	0.56	-141
1.99	0.78	119	0.07	-12	1.33	-4	0.57	-142
2.00	0.78	118	0.07	-12	1.34	-5	0.57	-142

NEL200101-24 Z_{in}/Z_{out}

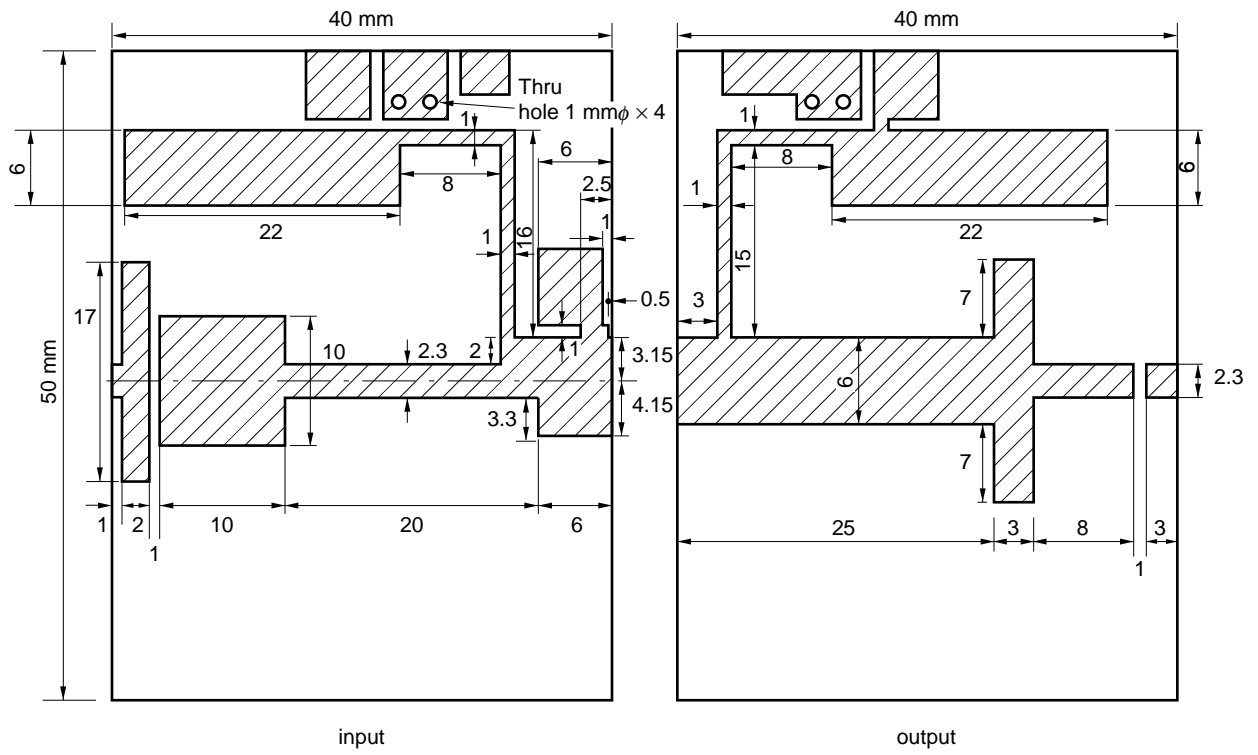


$Z_0 = 50 \text{ ohm}$

f [GHz]	Z_{in} [ohm]	Z_{out} [ohm]
1.80	$8.7 + j38$	$2.2 - j19$
1.90	$6.3 + j36$	$4.1 - j24$
1.97	$5.4 + j33$	$6.4 - j30$
2.00	$4.7 + j30$	$10 - j37$

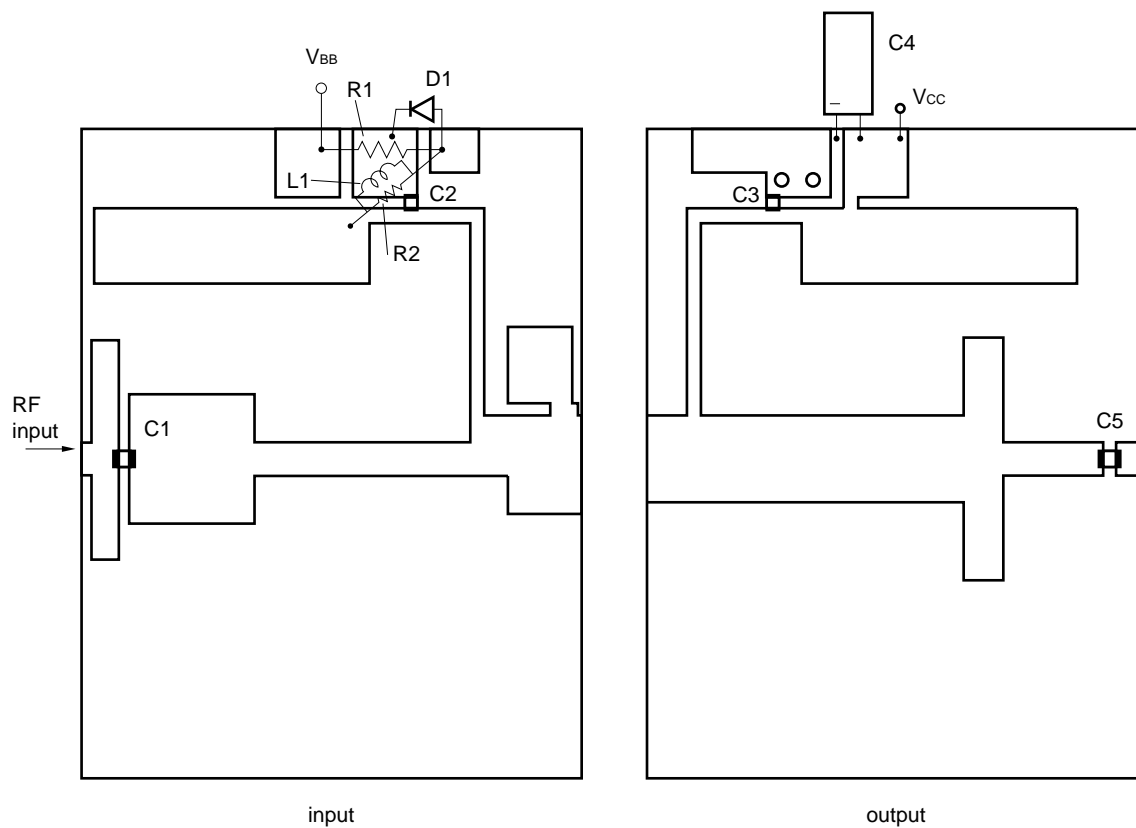


Circuit Drawing



SUBSTRATE (TEFLON)
 DICLAD 522T®
 THICKNESS = 0.79 mm
 DOUBLE SIDE 35 μ m Cu
 $\epsilon_r = 2.6$

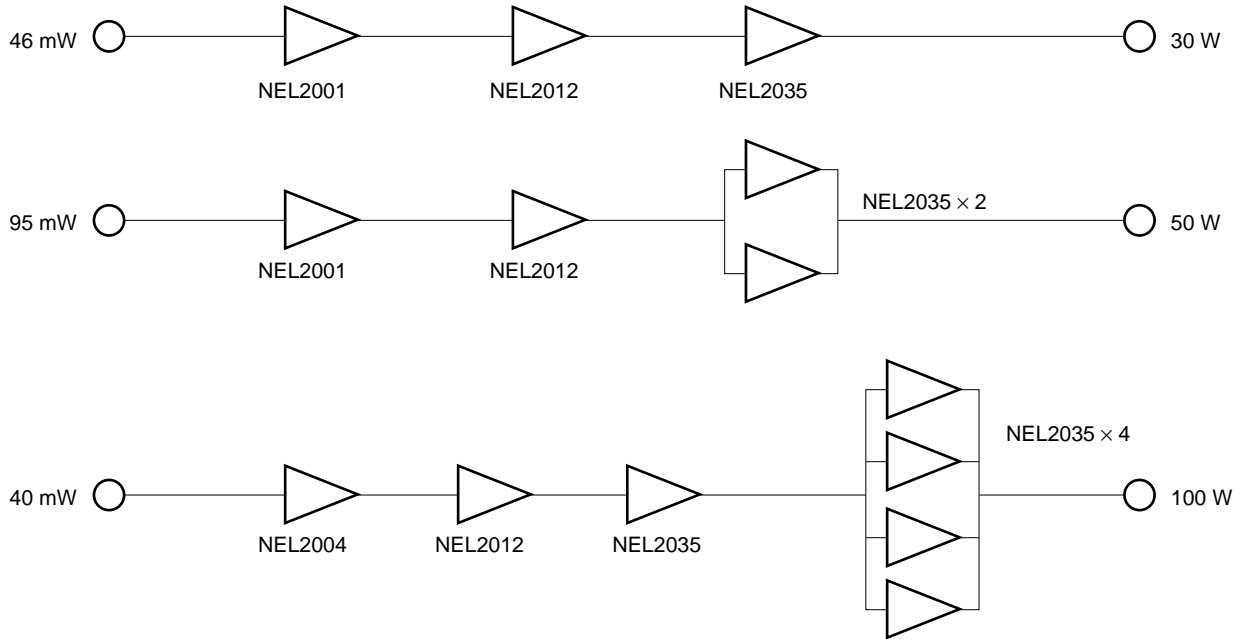
Components Layout



- R1: 5.1 Ω
- R2: 30 Ω
- L1: 5 mm ϕ 10T Coil
- D1: 1S2075
- C1, C2, C3, C5: MURATA, 47 pF
- C4: 22 μ F (50 V)
Electrolytic Capacitor

APPLICATION

= Amplifier Diagrams =



[MEMO]

[MEMO]

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